



Ultrafast recovery diode

Datasheet - production data

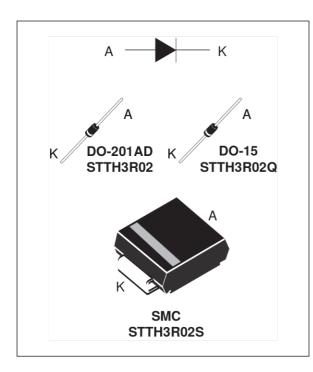


Table 1. Device summary

I _{F(AV)}	3 A
V_{RRM}	200 V
T _j (max)	175 °C
V _F (typ)	0.7 V
t _{rr} (typ)	16 ns

Features

- · Very low conduction losses
- · Negligible switching losses
- · Low forward and reverse recovery times
- High junction temperature

Description

The STTH3R02 uses ST's new 200 V planar Pt doping technology, and it is specially suited for switching mode base drive and transistor circuits.

Packaged in DO-201AD, DO-15, and SMC, this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection.

Characteristics STTH3R02

1 Characteristics

Table 2. Absolute ratings (limiting values at T_i = 25 °C, unless otherwise specified)

Symbol	Paramete	Value	Unit		
V _{RRM}	Repetitive peak reverse voltage		200	V	
I _{FRM}	Repetitive peak forward current	t _p = 5 μs, F = 5 kHz	110	Α	
	Forward rma augrent	DO-201AD / DO-15	70	۸	
F(RMS)	I _{F(RMS)} Forward rms current	SMC	70	Α	
		DO-15 T _{lead} = 50 °C		А	
I _{F(AV)}	Average forward current, $\delta = 0.5$	DO-201AD T _{lead} = 90 °C	3		
		SMC T _c = 110 °C			
I _{FSM}	Surge non repetitive forward current	t _p = 10 ms Sinusoidal	75	Α	
T _{stg}	Storage temperature range	-65 to + 175	°C		
T _j	Maximum operating junction tempera	175	°C		
TL	Maximum lead temperature for solder case	230	°C		

Table 3. Thermal parameters

Symbol		Parameter			
D	Junction to lead	Lead Length = 10 mm on infinite	DO-15	45	
$R_{th(j-l)}$	Junction to lead	heatsink DO-201AD	DO-201AD	30	°C/W
R _{th(j-c)}	lunction to case		SMC	20	

Table 4. Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I _R ⁽¹⁾	Reverse leakage	T _j = 25 °C	V _R = V _{RRM}			3	Δ
'R'	current	T _j = 125 °C	VR - VRRM		3	30	μΑ
	Forward voltage drop	T _j = 25 °C	I _F = 9 A			1.20	
V (2)		T _j = 25 °C			0.89	1.0	v
VF` ′		T _j = 100 °C	I _F = 3 A		0.76	0.85	\ \ \
		T _j = 150 °C			0.70	0.80	

^{1.} Pulse test: t_p = 5 ms, δ < 2 %

To evaluate the conduction losses use the following equation:

$$P = 0.68 \times I_{F(AV)} + 0.04 I_{F}^{2}(RMS)$$

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^{2.} Pulse test: t_p = 380 μ s, δ < 2 %

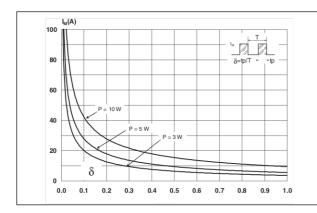
STTH3R02 Characteristics

Table 5. Dynamic characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t _{rr}	Reverse recovery time	$I_F = 1 \text{ A, } dI_F/dt = -50 \text{ A/}\mu\text{s,}$ $V_R = 30 \text{ V, } T_j = 25 \text{ °C}$		24	30	ns
'rr	Theverse recovery time	$I_F = 1 \text{ A, } dI_F/dt = -100 \text{ A/}\mu\text{s,}$ $V_R = 30 \text{ V, } T_j = 25 \text{ °C}$		16	20	113
I _{RM}	Reverse recovery current	$I_F = 3 \text{ A}, dI_F/dt = -200 \text{ A/}\mu\text{s},$ $V_R = 160 \text{ V}, T_j = 125 ^{\circ}\text{C}$		3.5	4.5	Α
t _{fr}	Forward recovery time	$I_F = 3~A,~dI_F/dt = 100~A/\mu s$ $V_{FR} = 1.1~x~V_{Fmax},~T_j = 25~^{\circ}C$		40		ns
V _{FP}	Forward recovery voltage	$I_F = 3 \text{ A, } dI_F/dt = 100 \text{ A/}\mu\text{s,}$ $T_j = 25 ^{\circ}\text{C}$		1.9		V

Figure 1. peak current versus duty cycle

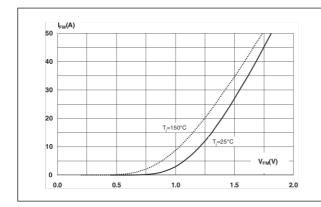
Figure 2. Forward voltage drop versus forward current (typical values)

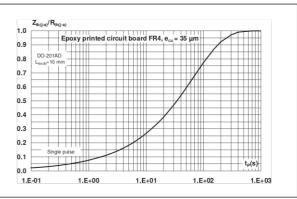


10 T_F150°C V_{FM}(V) 0.0 0.5 1.0 1.5 2.0

Figure 3. Forward voltage drop versus forward current (maximum values)

Figure 4. Relative variation of thermal impedance junction to ambient versus pulse duration - DO-201AD

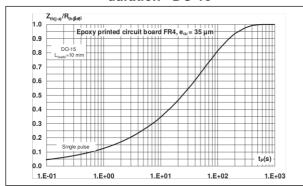




Characteristics STTH3R02

Figure 5. Relative variation of thermal impedance junction to ambient versus pulse duration - DO-15

Figure 6. Relative variation of thermal impedance junction to ambient versus pulse duration - SMC



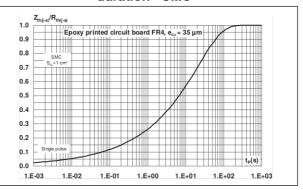
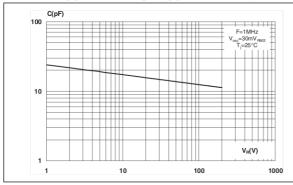


Figure 7. Junction capacitance versus reverse applied voltage (typical values)

Figure 8. Reverse recovery charges versus dl_F/dt (typical values)



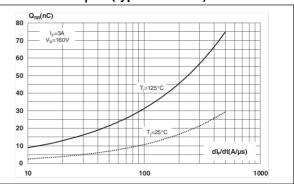
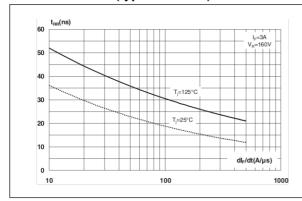
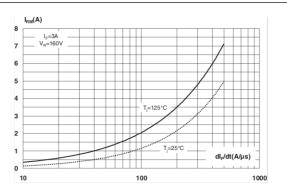


Figure 9. Reverse recovery time versus dI_F/dt (typical values)

Figure 10. Peak reverse recovery current versus dl_F/dt (typical values)





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Figure 11. Dynamic parameters versus junction temperature

Figure 12. Thermal resistance junction to ambient versus copper surface under each lead

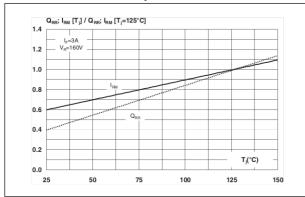
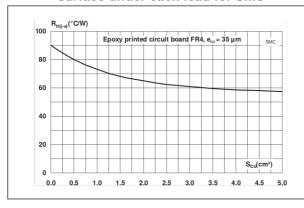
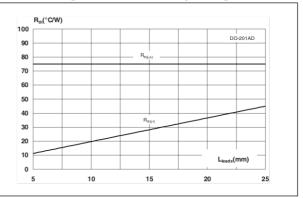


Figure 13. Thermal resistance versus copper surface under each lead for SMC

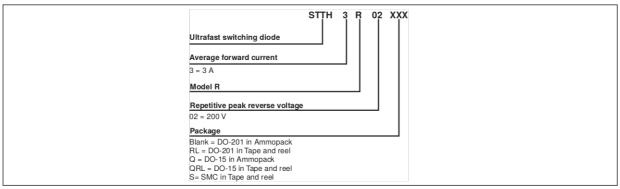
Figure 14. Thermal resistance versus lead length for DO-201AD package





2 Ordering information scheme

Figure 15. Ordering information scheme





Package information STTH3R02

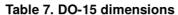
3 Package information

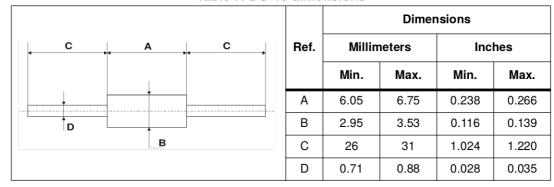
- Epoxy meets UL94, V0
- Cooling method: by conduction (C)

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Dimensions Ref. **Millimeters** Inches Min. Max. Min. Max. Α 9.50 0.374 В 25.40 1.000 С 5.30 0.209 D 1.30 0.051 Ε 1.25 0.049 1 - The lead diameter ø D is not controlled over zone E 2 - The minimum length which must stay Notes straight between the right angles after bending is 0.59"(15mm)

Table 6. DO-201AD dimensions

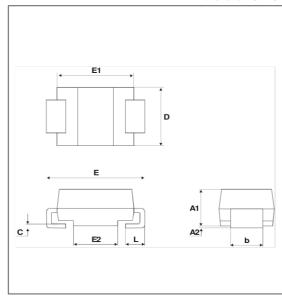






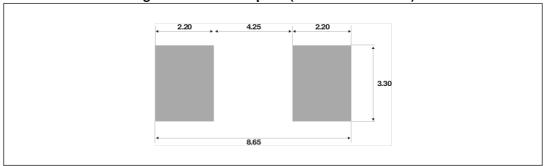
STTH3R02 Package information

Table 8. SMC dimensions



	Dimensions				
Ref.	Millimeters		Inc	hes	
	Min.	Max.	Min.	Max.	
A1	1.90	2.45	0.075	0.096	
A2	0.05	0.20	0.002	0.008	
b	2.90	3.2	0.114	0.126	
С	0.15	0.41	0.006	0.016	
Е	7.75	8.15	0.305	0.321	
E1	6.60	7.15	0.260	0.281	
E2	4.40	4.70	0.173	0.185	
D	5.55	6.25	0.218	0.246	
L	0.75	1.60	0.030	0.063	

Figure 16. SMC footprint (dimensions in mm)



Ordering information STTH3R02

4 Ordering information

Table 9. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STTH3R02	STTH3R02	DO-201AD	1.16 g	600	Ammopack
STTH3R02RL	STTH3R02	DO-201AD	1.16 g	1900	Tape and reel
STTH3R02Q	STTH3R02	DO-15	0.4 g	1000	Ammopack
STTH3R02QRL	STTH3R02	DO-15	0.4 g	6000	Tape and reel
STTH3R02S	3R2S	SMC	0.243 g	2500	Tape and reel

5 Revision history

Table 10. Document revision history

Date	Revision	Changes
03-May-2006	1	First issue.
10-Oct-2006	2	Added SMC package.
17-Apr-2014	3	Updated ECOPACK statement. Reformatted to current standards.

DocID12359 Rev 3

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